# мисм 2W C/X-Band Power Amplifier

4.5-9.0 GHz

**Preliminary Information** 

#### **Features**

- ◆ 4.5 to 9.0 GHz Operation
- 2 Watt Saturated Output Power Level
- ♦ Variable Drain Voltage (4-10V) Operation
- ◆ Self-Aligned MSAG® MESFET Process

## **Primary Applications**

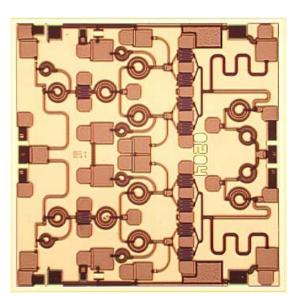
- Multiple Band Point-to-Point Radio
- SatCom
- ♦ ISM Band

#### **Description**

The MAAPGM0021-Die is a 2-stage 2 W power amplifier with on-chip bias networks. This product is fully matched to 50 ohms on both the input and output. It can be used as a power amplifier stage or as a driver stage in high power applications.

Each device is 100% RF tested on wafer to ensure performance compliance. The part is fabricated using M/A-COM's repeatable, high performance and highly reliable GaAs Multifunction Self-Aligned Gate (MSAG®) MESFET Process. This process provides polyimide scratch protection.

#### 4.5-9.0 GHz GaAs MMIC Amplifier



#### Electrical Characteristics: $T_B = 40^{\circ}C^1$ , $Z_0 = 50\Omega$ , $V_{DD} = 8V$ , $V_{GG} = -2V$ , $P_{in} = 18$ dBm

Parameter	Symbol	Typical	Units	
Bandwidth	f	4.5-9.0	GHz	
Output Power	POUT	33	dBm	
Power Added Efficiency	PAE	30	%	
1-dB Compression Point	P1dB	31	dBm	
Small Signal Gain	G	17	dB	
Input VSWR	VSWR	1.7:1		
Gate Current	IGG	< 2	mA	
Drain Current	IDD	< 750	mA	
Output Third Order Intercept	ОТОІ	41	dBm	
Noise Figure	NF	9	dB	
3 <sup>rd</sup> Order Intermodulation Distortion Single Carrier Level = 23 dBm	IM3	31	dBc	
5 <sup>th</sup> Order Intermodulation Distortion Single Carrier Level = 23 dBm	IM5	41	dBc	

# Maximum Operating Conditions <sup>1</sup>

Parameter	Symbol	Absolute Maximum	Units
Input Power	P <sub>IN</sub>	23.0	dBm
Drain Supply Voltage	$V_{DD}$	+12.0	V
Gate Supply Voltage	$V_{GG}$	-3.0	V
Quiescent Drain Current (No RF)	I <sub>DQ</sub>	950	mA
Quiescent DC Power Dissipated (No RF)	P <sub>DISS</sub>	6.3	W
Junction Temperature	T <sub>j</sub>	180	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

<sup>1.</sup> Operation outside of these ranges may reduce product reliability. Operation at other than the typical values may result in performance outside the guaranteed limits.

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min	Тур	Max	Unit
Drain Voltage	$V_{DD}$	4.0	8.0	10.0	V
Gate Voltage	$V_{GG}$	-2.3	-2.0	-1.5	V
Input Power	P <sub>IN</sub>		18.0	21.0	dBm
Junction Temperature	TJ			150	°C
Thermal Resistance	$\Theta_{JC}$		12.7°	150	°C/W
MMIC Base Temperature	T <sub>B</sub>			Note 2	°C

<sup>2.</sup> Maximum MMIC Base Temperature = 150°C -  $\Theta_{JC}^* V_{DD} * I_{DQ}$ 

# **Operating Instructions**

This device is static sensitive. Please handle with care. To operate the device, follow these steps.

- 1. Apply  $V_{GG}$  = -2 V,  $V_{DD}$ = 0 V.
- 2. Ramp V<sub>DD</sub> to desired voltage, typically 8 V.
- 3. Adjust  $V_{\text{GG}}$  to set  $I_{\text{DQ}}$ , (approximately @ -2 V).
- 4. Set RF input.
- 5. Power down sequence in reverse. Turn  $V_{\text{GG}}$  off last.



Specifications subject to change without notice.

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# 2W C/X-Band Power Amplifier

## **MAAPGM0021-DIE**

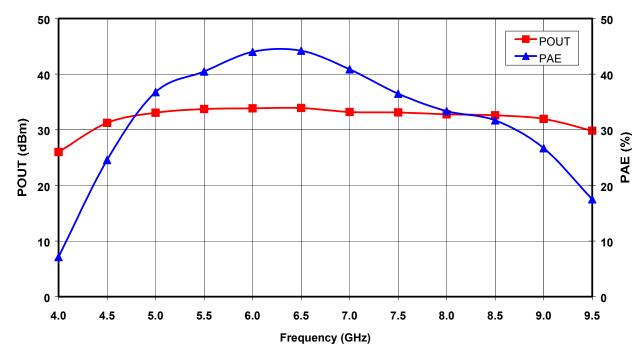


Figure 1. Output Power and Power Added Efficiency vs. Frequency at V<sub>DD</sub> = 8V and  $P_{in} = 18 dBm$ .

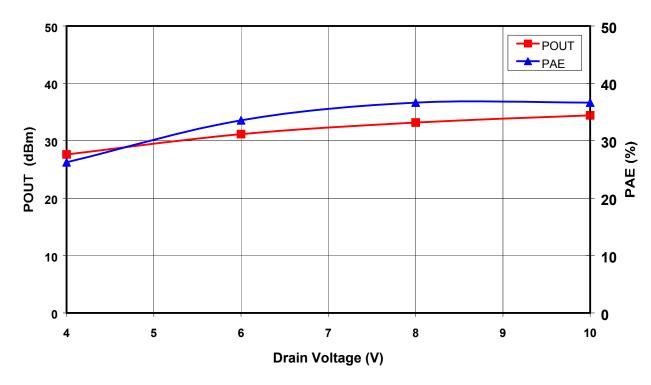


Figure 2. Saturated Output Power and Power Added Efficiency vs. Drain Voltage at fo = 7.5 GHz.

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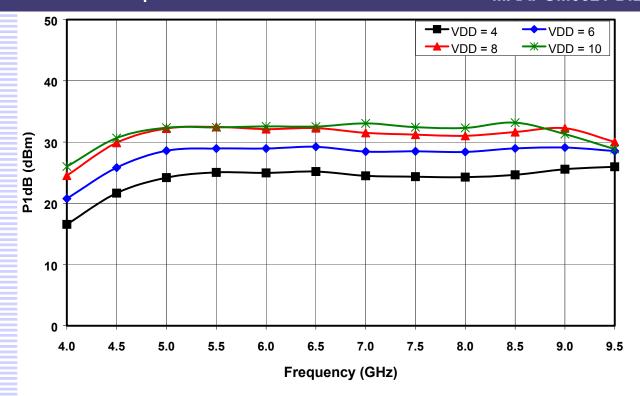


Figure 3. 1dB Compression Point vs. Drain Voltage

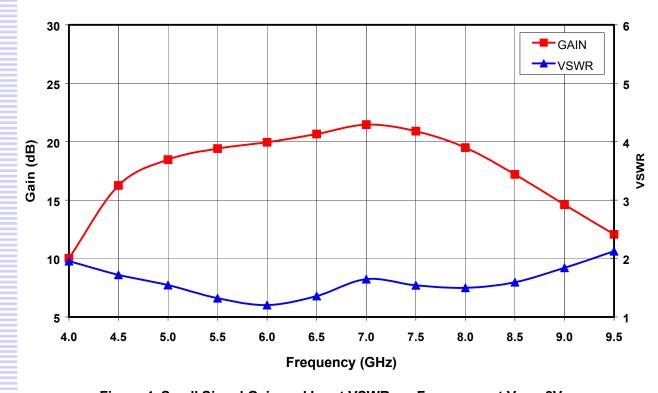


Figure 4. Small Signal Gain and Input VSWR vs. Frequency at  $V_{DD} = 8V$ .

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## **MAAPGM0021-DIE**

#### **Mechanical Information**

Chip Size: 2.98 x 2.98 x 0.075 mm (117 x 117 x 3 mils)

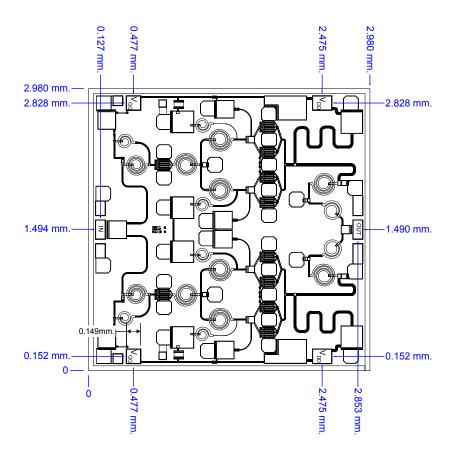


Figure 5. Die Layout

#### **Bond Pad Dimensions**

Pad	Size (μm)	Size (mils)
RF In and Out	100 x 200	4 x 8
DC Drain Supply Voltage VDD	200 x 150	8 x 6
DC Gate Supply Voltage VGG	150 x 150	6 x 6

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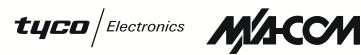
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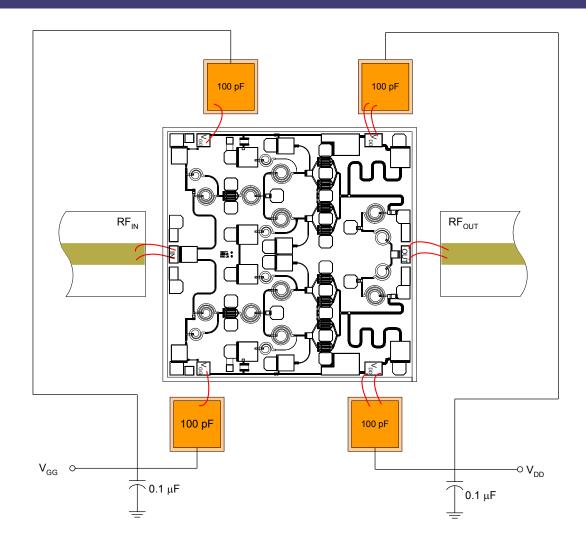
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## **MAAPGM0021-DIE**



**Figure 6. Recommended bonding diagram** for pedestal mount. Support circuitry typical of MMIC characterization fixture for CW testing.

#### **Assembly Instructions:**

Die attach: Use AuSn (80/20) 1-2 mil. preform solder. Limit time @ 300 °C to less than 5 minutes.

**Wirebonding:** Bond @ 160 °C using standard ball or thermal compression wedge bond techniques. For DC pad connections, use either ball or wedge bonds. For best RF performance, use wedge bonds of shortest length, although ball bonds are also acceptable.

Biasing Note: Must apply negative bias to  $V_{\text{GG}}$  before applying positive bias to  $V_{\text{DD}}$  to prevent damage to amplifier.

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